

isc N-Channel MOSFET Transistor

2SK2299

DESCRIPTION

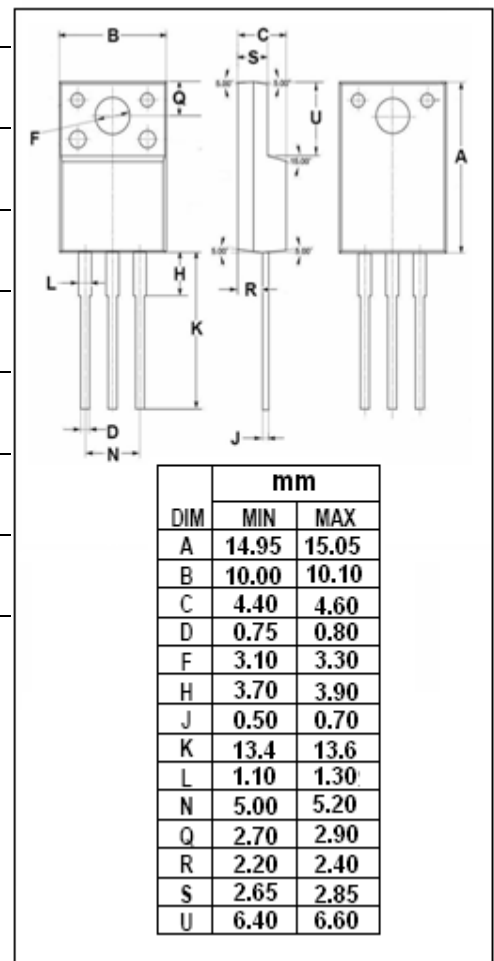
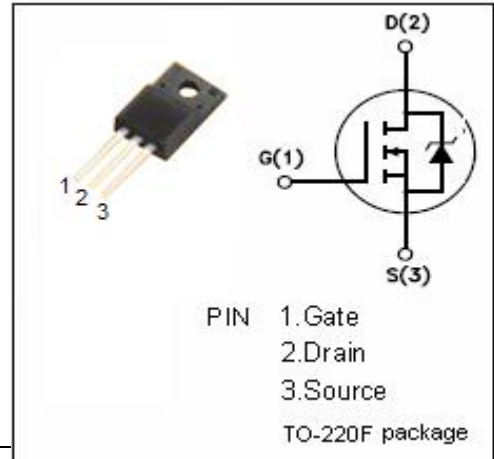
- Drain Current $I_D = 7A @ T_C = 25^\circ C$
- Drain Source Voltage-
: $V_{DSS} = 450V(\text{Min})$
- Fast Switching Speed

APPLICATIONS

- Switching Regulators

ABSOLUTE MAXIMUM RATINGS($T_a = 25^\circ C$)

SYMBOL	ARAMETER	VALUE	UNIT
V_{DSS}	Drain-Source Voltage ($V_{GS} = 0$)	450	V
V_{GS}	Gate-Source Voltage	± 30	V
I_D	Drain Current-continuous@ $T_C = 25^\circ C$	7	A
$I_{D(\text{puls})}$	Pulsed Drain Current	28	A
P_{tot}	Total Dissipation@ $T_C = 25^\circ C$	30	W
T_j	Max. Operating Junction Temperature	150	$^\circ C$
T_{stg}	Storage Temperature Range	-55~150	$^\circ C$



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• ELECTRICAL CHARACTERISTICS ($T_C=25^\circ\text{C}$)

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP E	MAX	UNIT
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0; I_D=10\text{mA}$	450			V
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=10\text{V}; I_D=1\text{mA}$	2.0		4.0	V
$R_{DS(on)}$	Drain-Source On-Resistance	$V_{GS}=10\text{V}; I_D=4\text{A}$		0.85	1.1	Ω
I_{GSS}	Gate-Body Leakage Current	$V_{GS}=\pm 30\text{V}; V_{DS}=0$			± 100	nA
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=450\text{V}; V_{GS}=0$			100	μA
C_{iss}	Input Capacitance	$V_{DS}=10\text{V};$		870		pF
C_{rss}	Reverse Transfer Capacitance	$V_{GS}=0\text{V};$		40		
C_{oss}	Output Capacitance	$f_T=1\text{MHz}$		180		
t_r	Rise Time	$V_{GS}=10\text{V};$		18		ns
$t_{d(on)}$	Turn-on Delay Time	$R_{GS}=10\Omega$		15		
t_f	Fall Time	$I_D=4\text{A};$		35		
$t_{d(off)}$	Turn-off Delay Time	$V_{DD}=150\text{V};$		60		
		$R_L=37.5\Omega$				